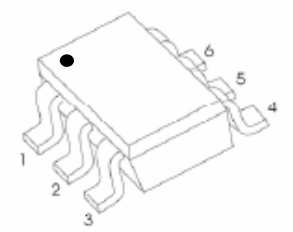
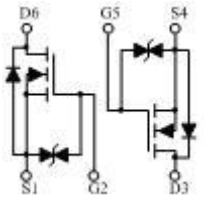
SOT-363 Plastic-Encapsulate MOSFETS

CJ3134KDW Dual N-Channel MOSFET

SOT-363





FEATURE

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- Equivalent to Two CJ3134K

APPLICATION

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

MARKING: 34K

ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	20	V
Gate-source voltage	V_{GS}	±12	V
Continuous drain current (t ≤10s)	I_D	0.75	A
Power dissipation*	P_D	0.15	W
Thermal resistance from junction to ambient	$R_{\theta JA}$	833	℃/W
Junction temperature	T_J	150	℃
Storage temperature	T_{stg}	-55~ +150	℃

* Repetitive rating : Pulse width limited by junction temperature.

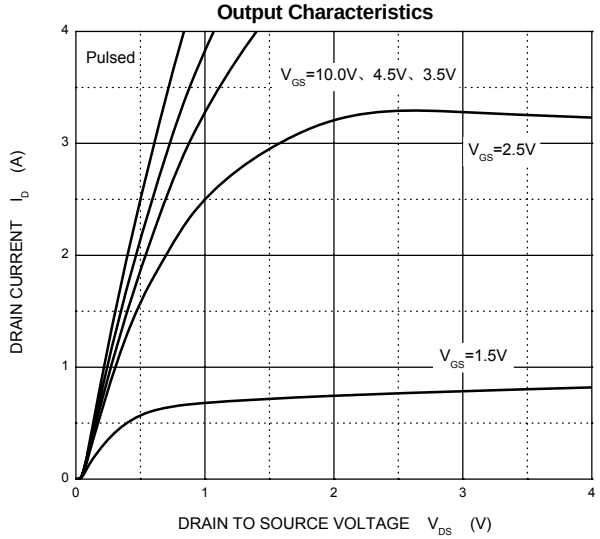
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =20V,V_{GS} = 0V			1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V			±50	μA
Gate threshold voltage (note 1)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.35		1	V
Drain-source on-resistance (note 1)	$R_{DS(on)}$	V_{GS} =4.5V, I_D =0.65A			380	mΩ
		V_{GS} =2.5V, I_D =0.55A			450	mΩ
		V_{GS} =1.8V, I_D =0.45A			800	mΩ
Forward tranconductance (note 1)	g_{FS}	V_{DS} =10V, I_D =0.8A		1.6		S
Diode forward voltage(note 1)	V_{SD}	I_S=0.15A, V_{GS} = 0V			1.2	V
DYNAMIC PARAMETERS (note 2)						
Input Capacitance	C_{iss}	V_{DS} =16V,V_{GS} =0V,f =1MHz		79	120	pF
Output Capacitance	C_{oss}			13	20	pF
Reverse Transfer Capacitance	C_{rss}			9	15	pF
SWITCHING PARAMETERS(note 2)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=4.5V,V_{DS}=10V, I_D=0.5A,R_{GEN}=10Ω		6.7		ns
Turn-on rise time	t_r			4.8		ns
Turn-off delay time	$t_{d(off)}$			17.3		ns
Turn-off fall time	t_f			7.4		ns
Total Gate Charge	Q_g	V_{DS} =10V,V_{GS} =4.5V,I_D =7A		20		nC
Gate-Source Charge	Q_{gs}			1		nC
Gate-Drain Charge	Q_{gd}			4		nC

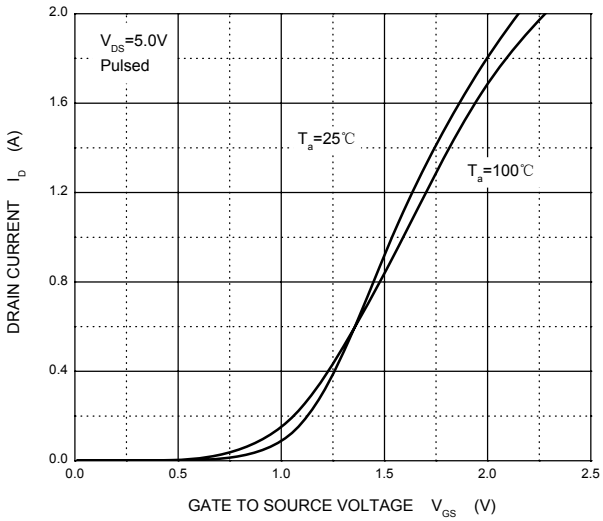
Notes :

1. Pulse Test : Pulse width≤300μs, duty cycle≤0.5%.
2. Guaranteed by design, not subject to production testing.

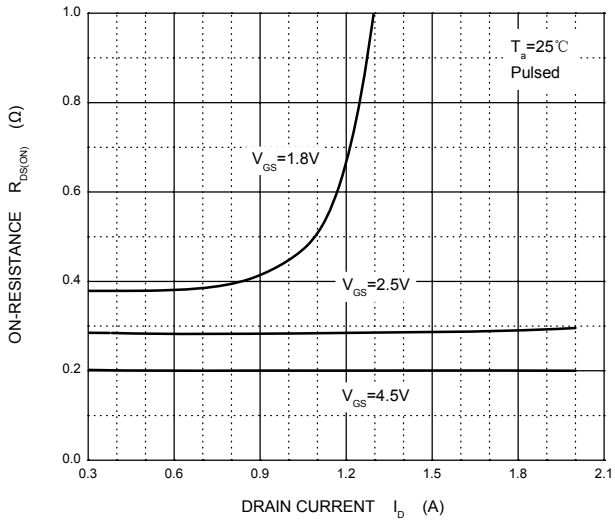
Output Characteristics



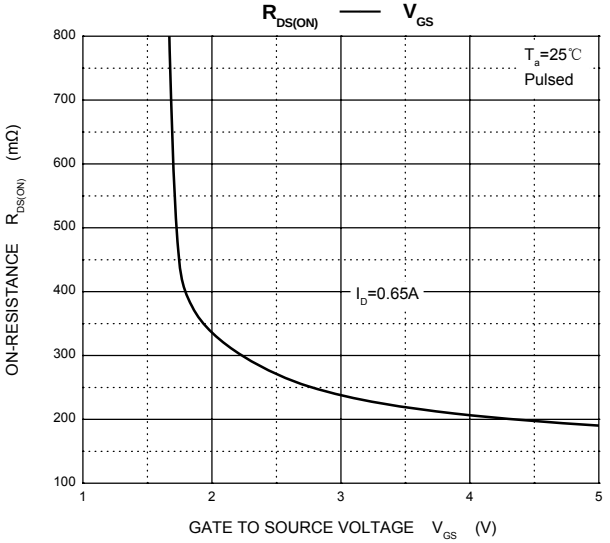
Transfer Characteristics



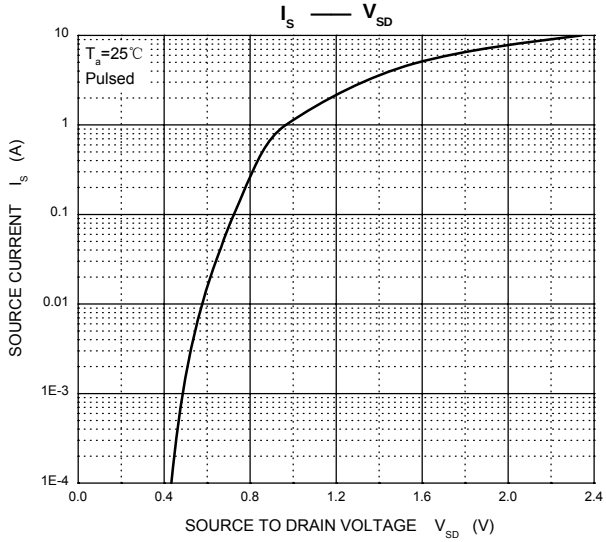
$R_{DS(ON)}$ —— I_D



$R_{DS(ON)}$ —— V_{GS}



I_S —— V_{SD}



Threshold Voltage